

Judul:

Investigation of annealing effect on the forward bias and leakage current changes of P-Type 6H-Sic schottky diodes with SiO₂ ramp profile after irradiated UP To 1.75 MGY (Application for nuclear fuel elements facilities)

Pengarang/Penulis:

Subjek:

Leakage

Nomor Panggil:

Penerbitan:

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